

Low-Voltage, Sub-Ohm, SPDT Analog Switch

DESCRIPTION

The DG2711 is a sub-ohm single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 25 ns, t_{OFF} : 14 ns), low on-resistance ($r_{DS(on)}$: 0.44 Ω) and small physical size (SC70), the DG2711 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2711 is built on Vishay Siliconix's low voltage submicron CMOS process. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG2711.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with 100 % matte tin device terminations, the lead (Pb)-free "-E3" suffix is being used as a designator.

FEATURES

- Low Voltage Operation (1.6 V to 3.6 V)
- Low On-Resistance - $r_{DS(on)}$: 0.44 Ω Typ.
- Fast Switching - t_{ON} : 25 ns, t_{OFF} : 14 ns
- Low Leakage
- TTL/CMOS Compatible
- 6-Pin SC-70 Package


RoHS
COMPLIANT

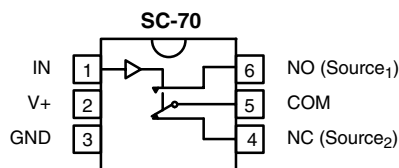
BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Top View

Device Marking: E8xx

TRUTH TABLE		
Logic	NC	NO
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION		
Temp Range	Package	Part Number
- 40 to 85 °C	SC70-6	DG2711DL-T1-E3



ABSOLUTE MAXIMUM RATINGS			
Parameter		Limit	Unit
Reference V+ to GND		- 0.3 to + 4	V
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	
Continuous Current (NO, NC and COM Pins)		± 200	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 300	
Storage Temperature	(D Suffix)	- 65 to 150	°C
Power Dissipation (Packages) ^b	6-Pin SO70 ^c	250	mW

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 3.1 mW/°C above 70 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+ = 1.8 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 1.8 V, ± 10 %, V _{IN} = 0.4 V or 1.0 V ^e	Temp ^a	Limits - 40 to 85 °C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 1.8 V, V _{COM} = 0.9 V I _{NO} , I _{NC} = 100 mA	Room Full		0.8	2.0 2.5	Ω
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 2.2 V, V _{NO} , V _{NC} = 0.2 V/2 V, V _{COM} = 2 V/0.2 V	Room Full ^d	- 1 - 10		1 10	nA
	I _{COM(off)}		Room Full ^d	- 1 - 10		1 10	
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 2.2 V, V _{NO} , V _{NC} = V _{COM} = 0.2 V/2 V	Room Full ^d	- 1 - 10		1 10	
Digital Control							
Input High Voltage	V _{INH}		Full	1.0			V
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance ^d	C _{in}		Full		5		pF
Input Current ^f	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 300 Ω, C _L = 35 pF Figures 1 and 2	Room Full ^d		36	60 62	ns
Turn-Off Time ^d	t _{OFF}		Room Full		22	42 44	
Break-Before-Make Time ^d	t _d		Room	3			
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω, Figure 3	Room		20		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		- 56		dB
Crosstalk ^d	X _{TALK}		Room		- 56		
NO, NC Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		73		pF
Channel-On Capacitance ^d	C _{ON}		Room		167		

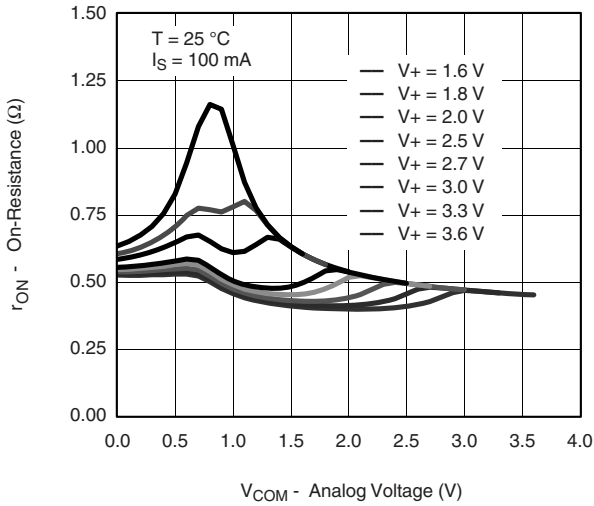


SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ± 10 %, VIN = 0.5 V or 1.4 V ^e	Temp ^a	Limits - 40 to 85 °C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V I _{NO} , I _{NC} = 100 mA	Room Full		0.44	0.6 0.7	Ω
r _{ON} Flatness	r _{ON} Flatness	V+ = 2.7 V, V _{COM} = 0.6 V, 1.5 V I _{NO} , I _{NC} = 100 mA	Room		0.14	0.2	
r _{ON} Match	Δr _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V I _{NO} , I _{NC} = 100 mA	Room			0.07	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V, V _{NO} , V _{NC} = 0.3 V/3 V, V _{COM} = 3 V/0.3 V	Room Full	- 1 - 10		1 10	nA
	I _{COM(off)}		Room Full	- 1 - 10		1 10	
Channel-On Leakage Current	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 0.3 V/3 V	Room Full	- 1 - 10		1 10	
Digital Control							
Input High Voltage	V _{INH}		Full	1.4			V
Input Low Voltage	V _{INL}		Full			0.5	
Input Capacitance ^d	C _{in}		Full		5		pF
Input Current ^f	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 1.5 V, R _L = 300 Ω, C _L = 35 pF Figures 1 and 2	Room Full		25	46 48	ns
Turn-Off Time	t _{OFF}		Room Full		14	38 40	
Break-Before-Make Time	t _d		Room	1			
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω, Figure 3	Room		28		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		- 56		dB
Crosstalk ^d	X _{TALK}		Room		- 56		
NO, NC Off Capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		70		pF
Channel-On Capacitance ^d	C _{ON}		Room		163		
Power Supply							
Power Supply Range	V+			1.6		3.6	V
Power Supply Current	I+	V+ = 3.6 V, V _{IN} = 0 or V+			0.01	1.0	μA

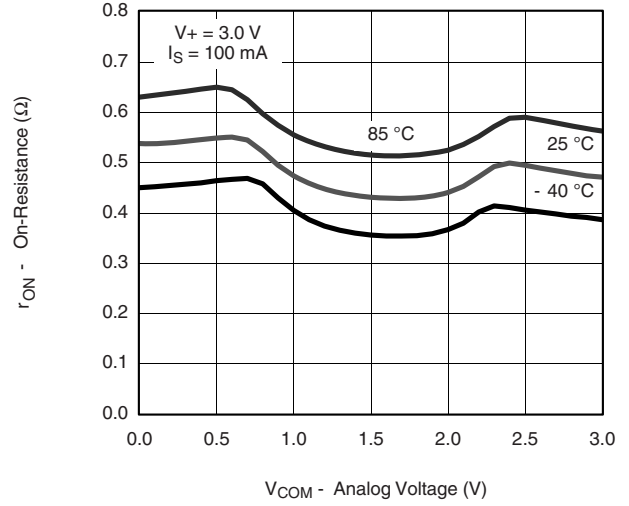
Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 3 V leakage testing, not production tested.

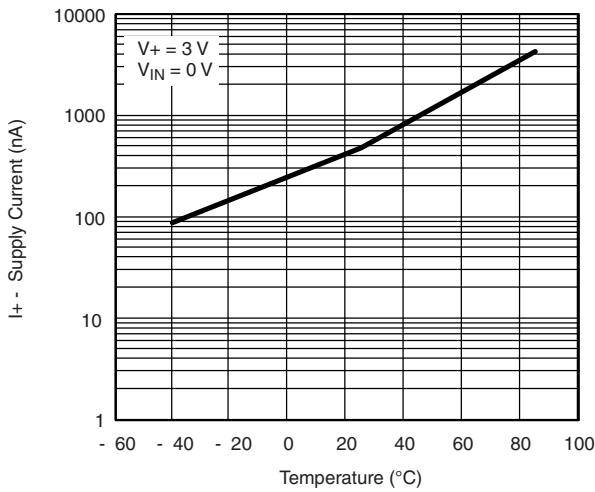
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



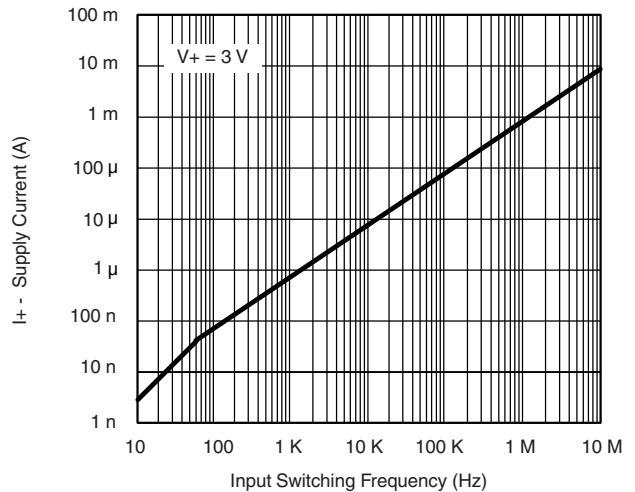
r_{ON} vs. V_{COM} and Single Supply Voltage



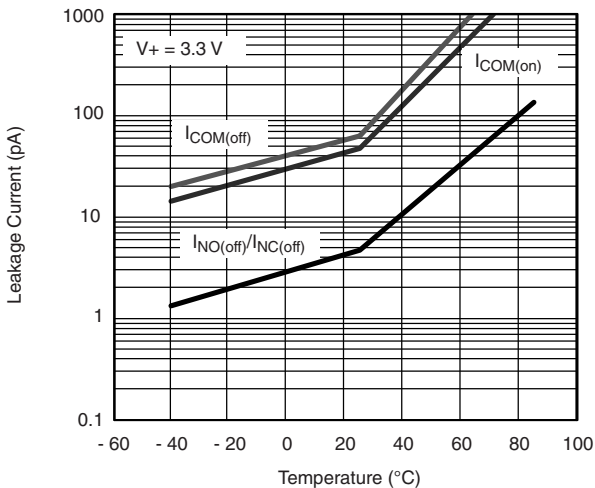
r_{ON} vs. Analog Voltage and Temperature



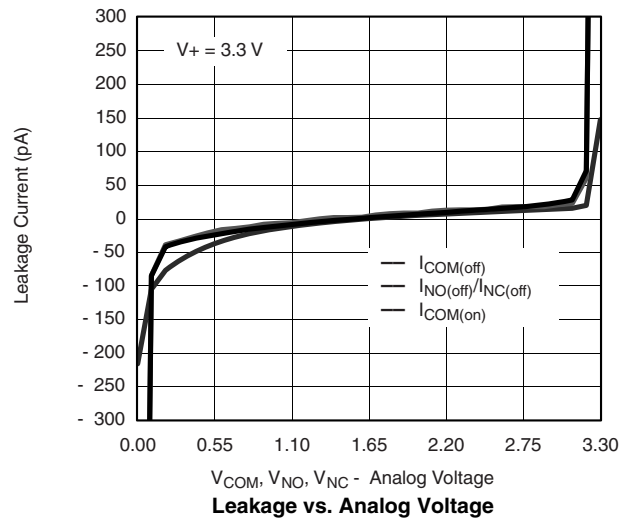
Supply Current vs. Temperature



Supply Current vs. Input Switching Frequency

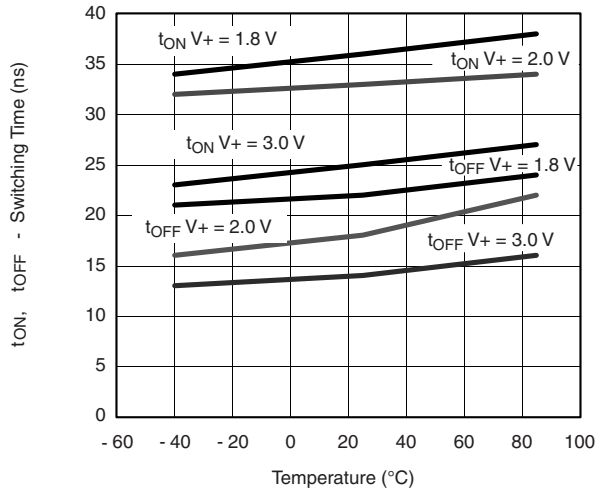


Leakage Current vs. Temperature

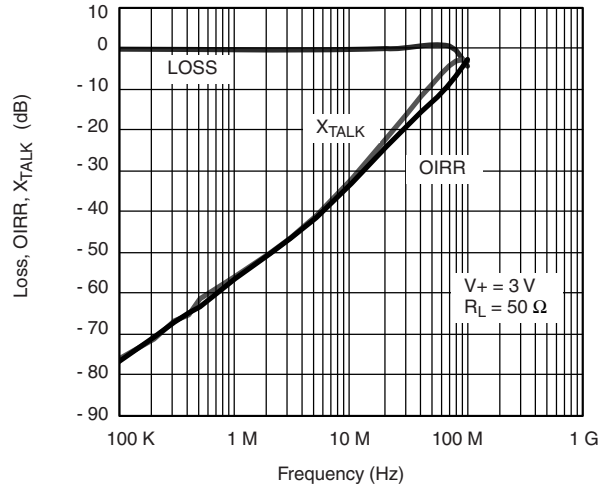


Leakage vs. Analog Voltage

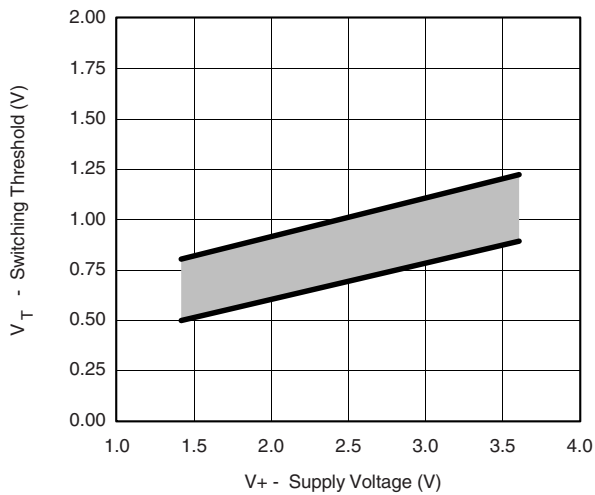
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



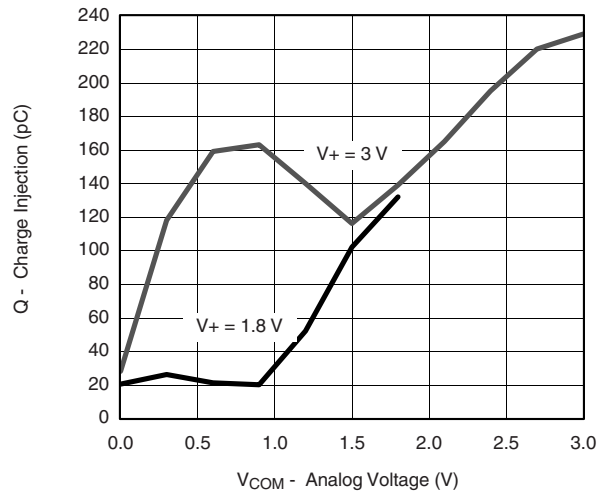
Switching Time vs. Temperature



Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

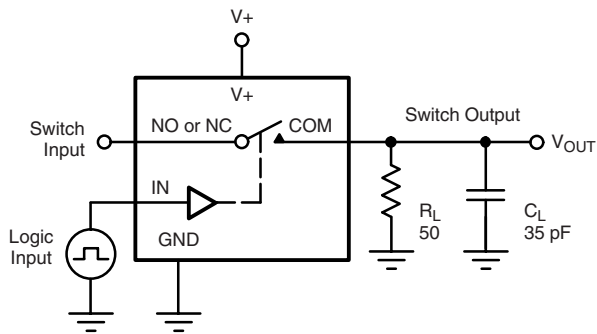


Switching Threshold vs. Supply Voltage



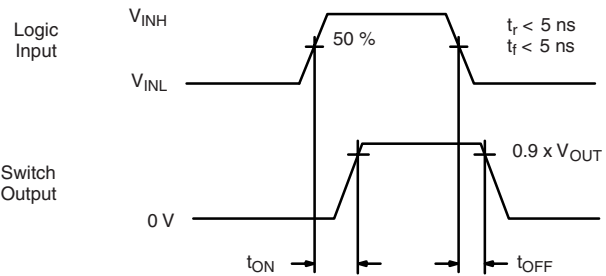
Charge Injection vs. Analog Voltage

TEST CIRCUITS



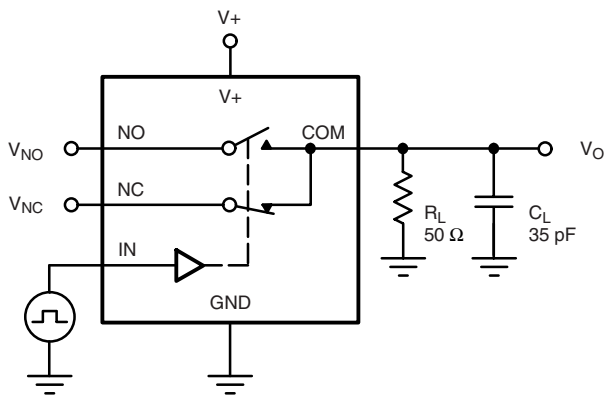
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On
 Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time



C_L (includes fixture and stray capacitance)

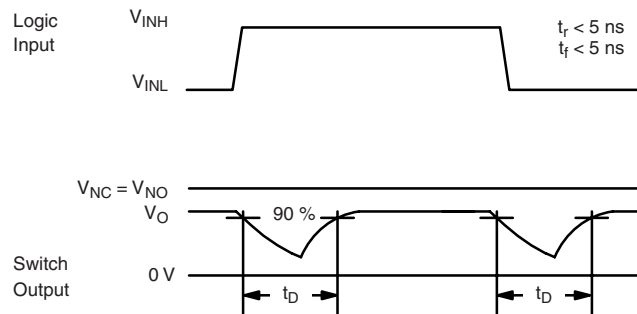
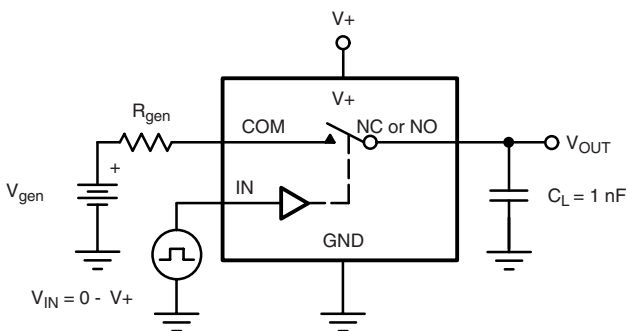
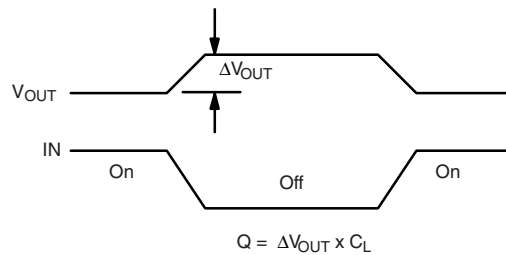


Figure 2. Break-Before-Make Interval



$V_{IN} = 0 - V_+$



IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

TEST CIRCUITS

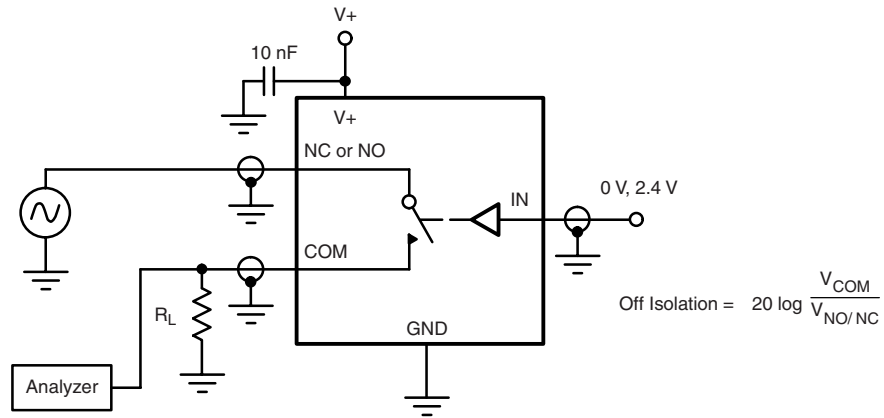


Figure 4. Off-Isolation

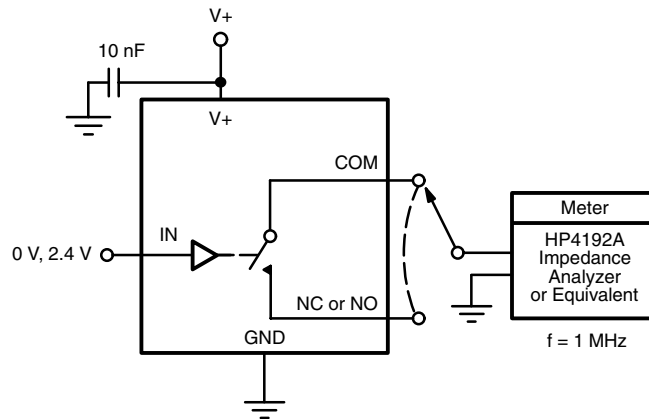


Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73200>.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.